

MOSFET – N-Channel POWERTRENCH®

75 V, 100 A, 3.7 mΩ

FDMS037N08B

Description

This N-Channel MOSFET is produced using onsemi's advanced POWERTRENCH process that has been tailored to minimize the on-state resistance and while maintaining superior switching performance.

Features

- $R_{DS(on)} = 3.01 \text{ m}\Omega$ (Typ.) @ $V_{GS} = 10 \text{ V}$, $I_D = 50 \text{ A}$
- Low FOM $R_{DS(on)} * Q_G$
- Low Reverse Recovery Charge, $Q_{rr} = 80 \text{ nC}$
- Soft Reverse Recovery Body Diode
- Enables Highly Efficiency in Synchronous Rectification
- Fast Switching Speed
- 100% UIL Tested
- These Device is Pb-Free and RoHS Compliant

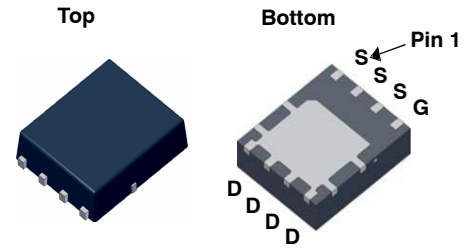
Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection circuit
- DC Motor Drives and Uninterruptible Power Supplies

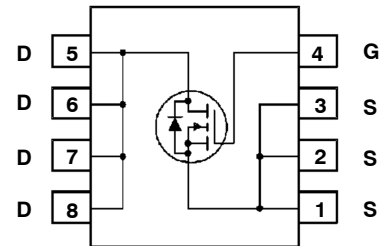
MOSFET MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Symbol	Parameter	Value	Unit
V_{DSS}	Drain to Source Voltage	75	V
V_{GSS}	Gate to Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_C = 25^\circ\text{C}$)	100	A
	– Continuous ($T_C = 25^\circ\text{C}$, Silicon Limited)	128	
	– Continuous ($T_A = 25^\circ\text{C}$) (Note 1a)	19.9	
I_{DM}	Drain Current – Pulsed (Note 2)	400	A
E_{AS}	Single Pulse Avalanche Energy (Note 3)	180.6	mJ
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	104.2	W
	Power Dissipation ($T_A = 25^\circ\text{C}$) (Note 1a)	0.83	
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

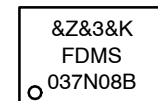
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



PQFN8 5X6, 1.27P
 (Power 56)
 CASE 483AE



MARKING DIAGRAM



&Z = Assembly Plant Code
 &3 = Numeric Date Code
 &K = 2-Digit Lot Code
 FDMS037N08B = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping†
FDMS037N08B	PQFN-8 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

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THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	1.2	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max (Note 1a)	50	

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	75	–	–	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu A$, Referenced to 25°C	–	39	–	mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 60 V, V_{GS} = 0 V$	–	–	1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20 V, V_{DS} = 0 V$	–	–	±100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	2.5	–	4.5	V
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = 10 V, I_D = 50 A$	–	3.01	3.7	mΩ
g_{FS}	Forward Transconductance	$V_{DS} = 10 V, I_D = 50 A$	–	108	–	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 37.5 V, V_{GS} = 0 V, f = 1 MHz$	–	4550	5915	pF
C_{oss}	Output Capacitance		–	1060	1380	pF
C_{rSS}	Reverse Transfer Capacitance		–	30.2	45	pF
$C_{oss(er)}$	Energy Releated Output Capacitance	$V_{DS} = 37.5 V, V_{GS} = 0 V$	–	1702	–	pF
$Q_{g(tot)}$	Total Gate Charge at 10 V	$V_{DS} = 37.5 V, I_D = 50 A$ $V_{GS} = 0 V$, to 10 V (Note 4)	–	76.8	100	nC
Q_{gs}	Gate to Source Gate Charge		–	27.5	–	nC
Q_{gd}	Gate to Drain “Miller” Charge		–	17.4	–	nC
$V_{plateau}$	Gate to Drain Plateau Voltage		–	5.1	–	V
Q_{sync}	Total Gate Charge Sync	$V_{DS} = 0 V, I_D = 50 A$	–	66.3	–	nC
Q_{oss}	Output Charge	$V_{DS} = 37.5 V, V_{GS} = 0 V$	–	74.6	–	nC
ESR	Equivalent Series Resistance	$f = 1 MHz$	–	1.28	–	Ω

Switching Characteristics

$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = 37.5 V, I_D = 50 A$, $V_{GS} = 10 V, R_G = 4.7 \Omega$ (Note 4)	–	34.9	80	ns
t_r	Turn–On Rise Time		–	20.1	50	ns
$t_{d(off)}$	Turn–Off Delay Time		–	55.3	120	ns
t_f	Turn–Off Fall Time		–	19.4	49	ns

Drain–Source Diode Characteristics and Maximum Ratings

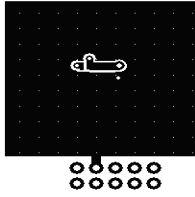
I_S	Maximum Continuous Drain to Source Diode Forward Current	–	–	100	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	–	–	400	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0 V, I_{SD} = 50 A$	–	–	1.3	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0 V, I_{SD} = 50 A$ $di_F/dt = 100 A/\mu s$	–	66.8	–	ns
Q_{rr}	Reverse Recovery Charge		–	84	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

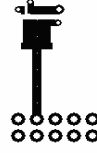
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NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a). 50 °C/W when mounted on a 1 in² pad of 2 oz copper.



b). 125 °C/W when mounted on a minimum pad of 2 oz copper.

2. Repetitive rating: pulse-width limited by maximum junction temperature.
3. $L = 0.3$ mH, $I_{AS} = 34.7$ A, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature typical characteristics.

TYPICAL CHARACTERISTICS

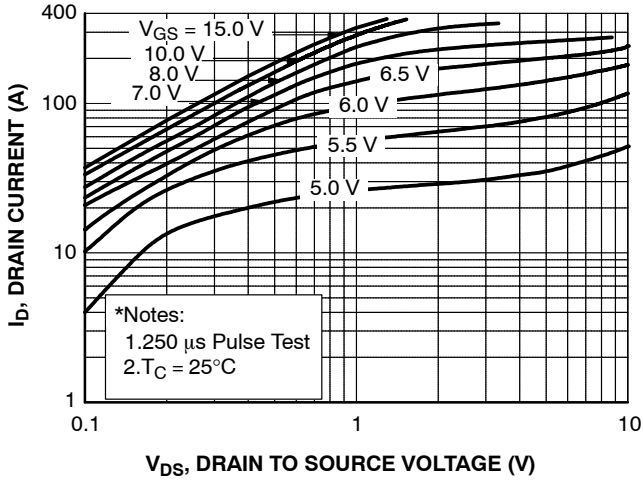


Figure 1. On-Region Characteristics

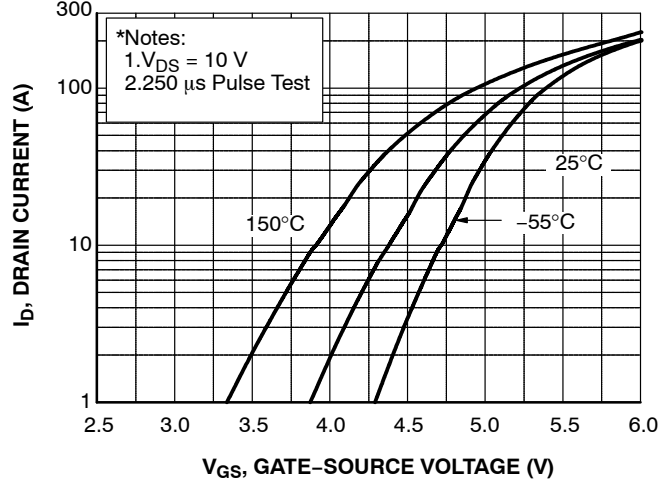


Figure 2. Transfer Characteristics

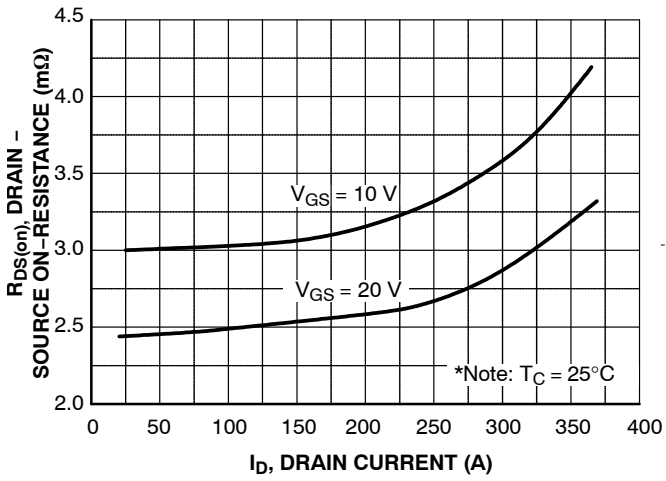


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

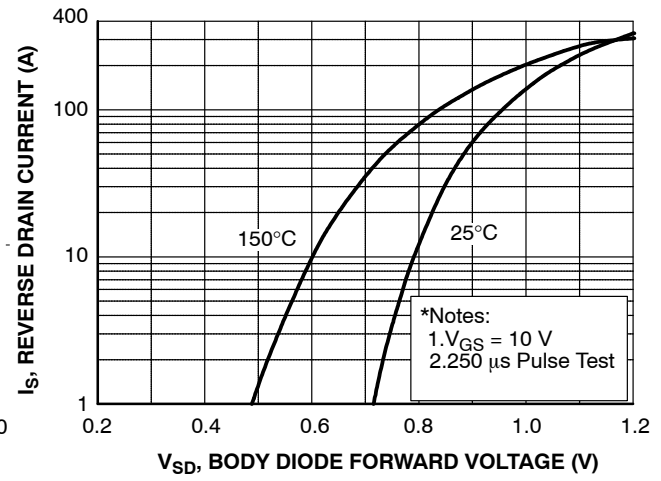


Figure 4. Body Diode Forward Voltage Variation vs Source Current and Temperature

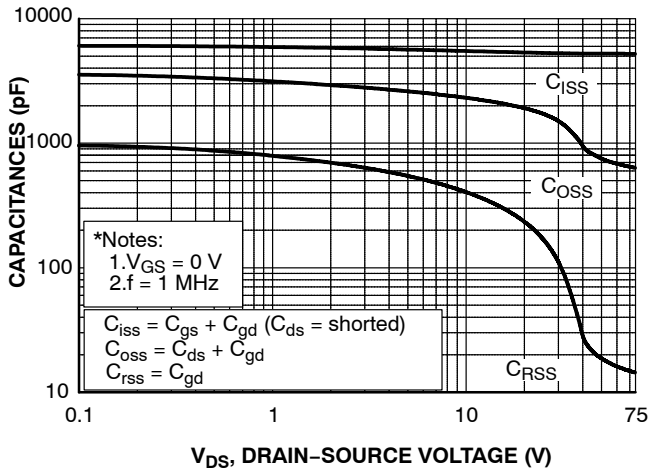


Figure 5. Capacitance Characteristics

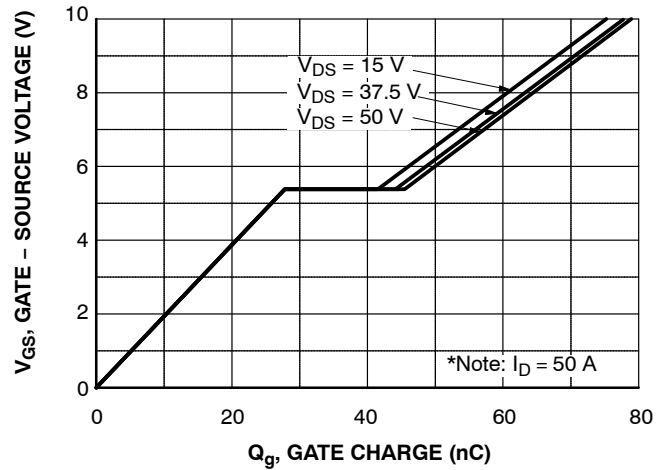


Figure 6. Gate Charge Characteristics

TYPICAL CHARACTERISTICS (CONTINUED)

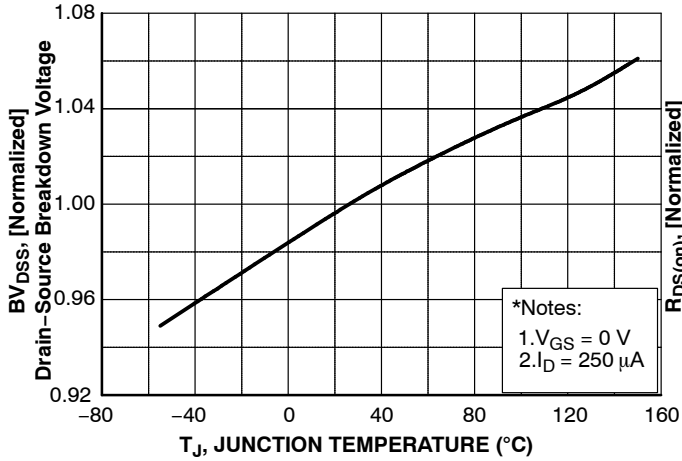


Figure 7. Breakdown Voltage Variation vs Temperature

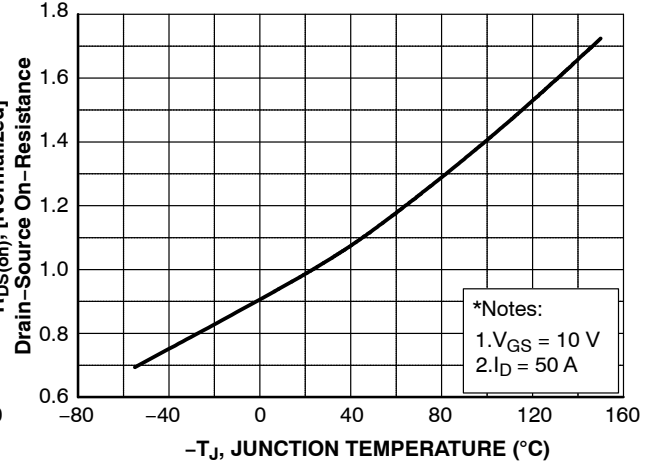


Figure 8. On-Resistance Variation vs Temperature

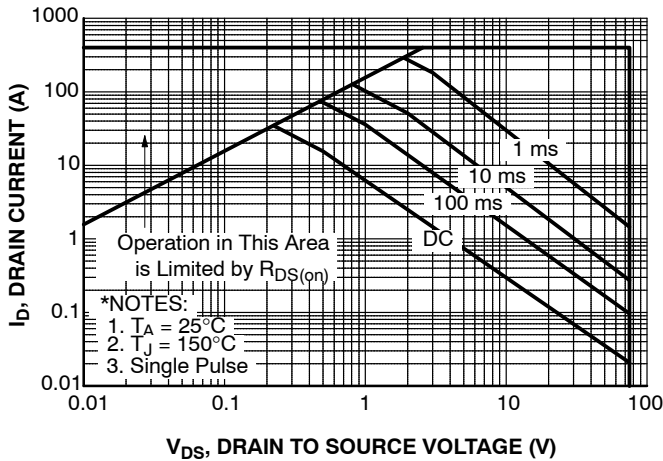


Figure 9. Maximum Safe Operating Area

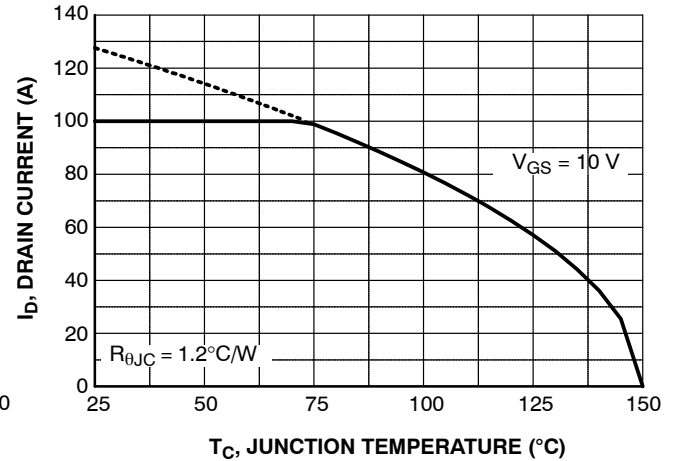


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

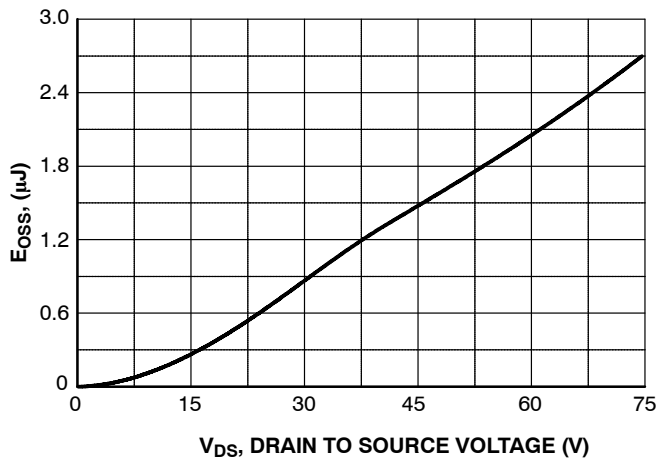


Figure 11. Eoss vs. Drain to Source Voltage

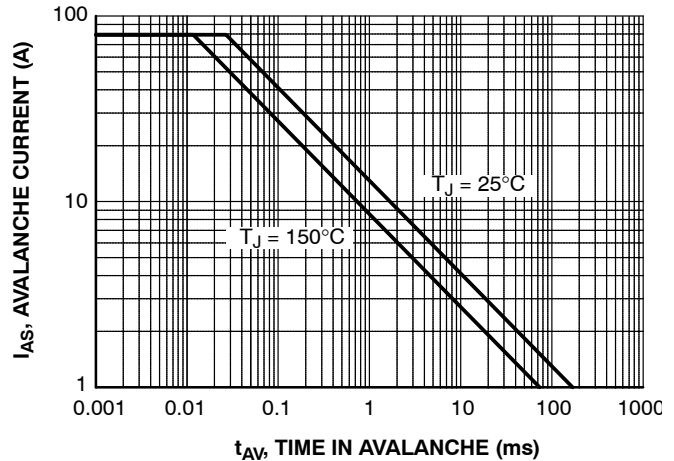


Figure 12. Unclamped Inductive Switching Capability

TYPICAL CHARACTERISTICS (CONTINUED)

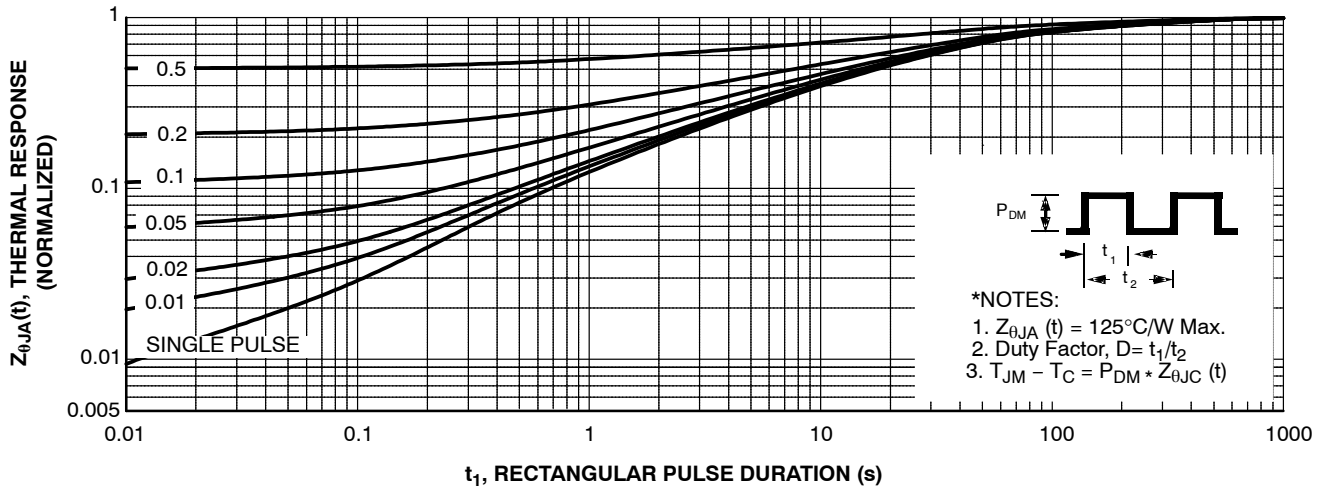


Figure 13. Transient Thermal Response Curve

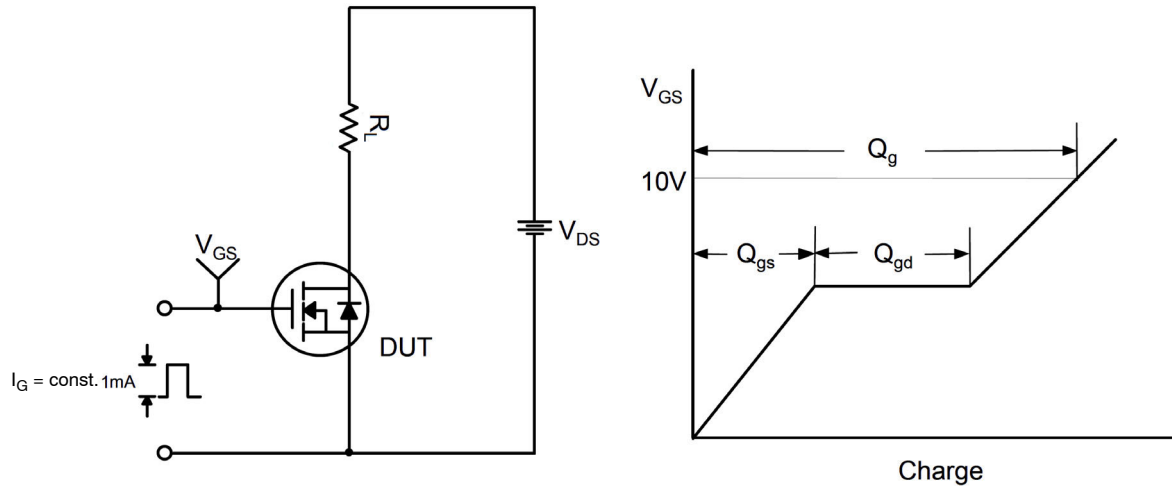


Figure 14. Gate Charge Test Circuit & Waveform

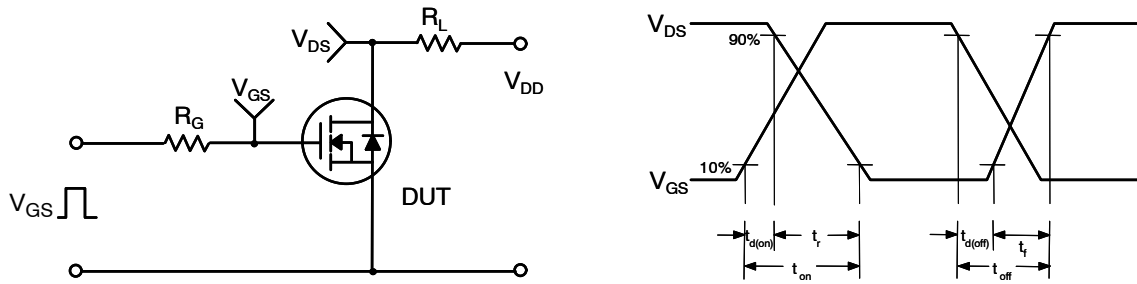


Figure 15. Resistive Switching Test Circuit & Waveforms

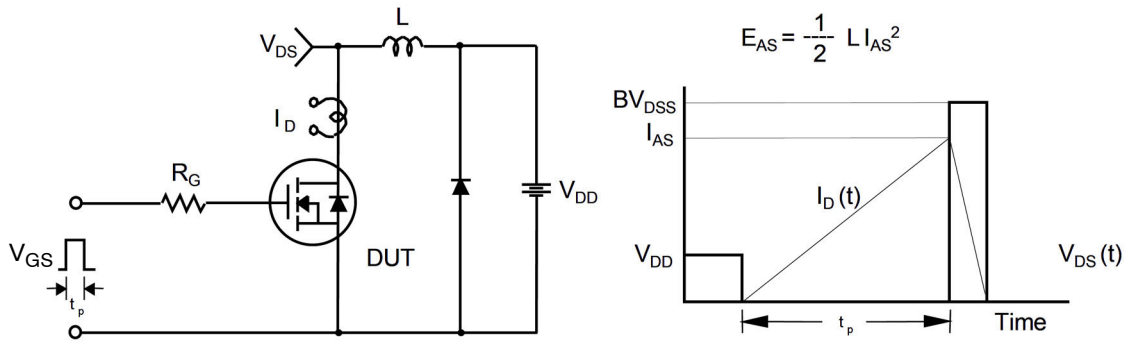


Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms

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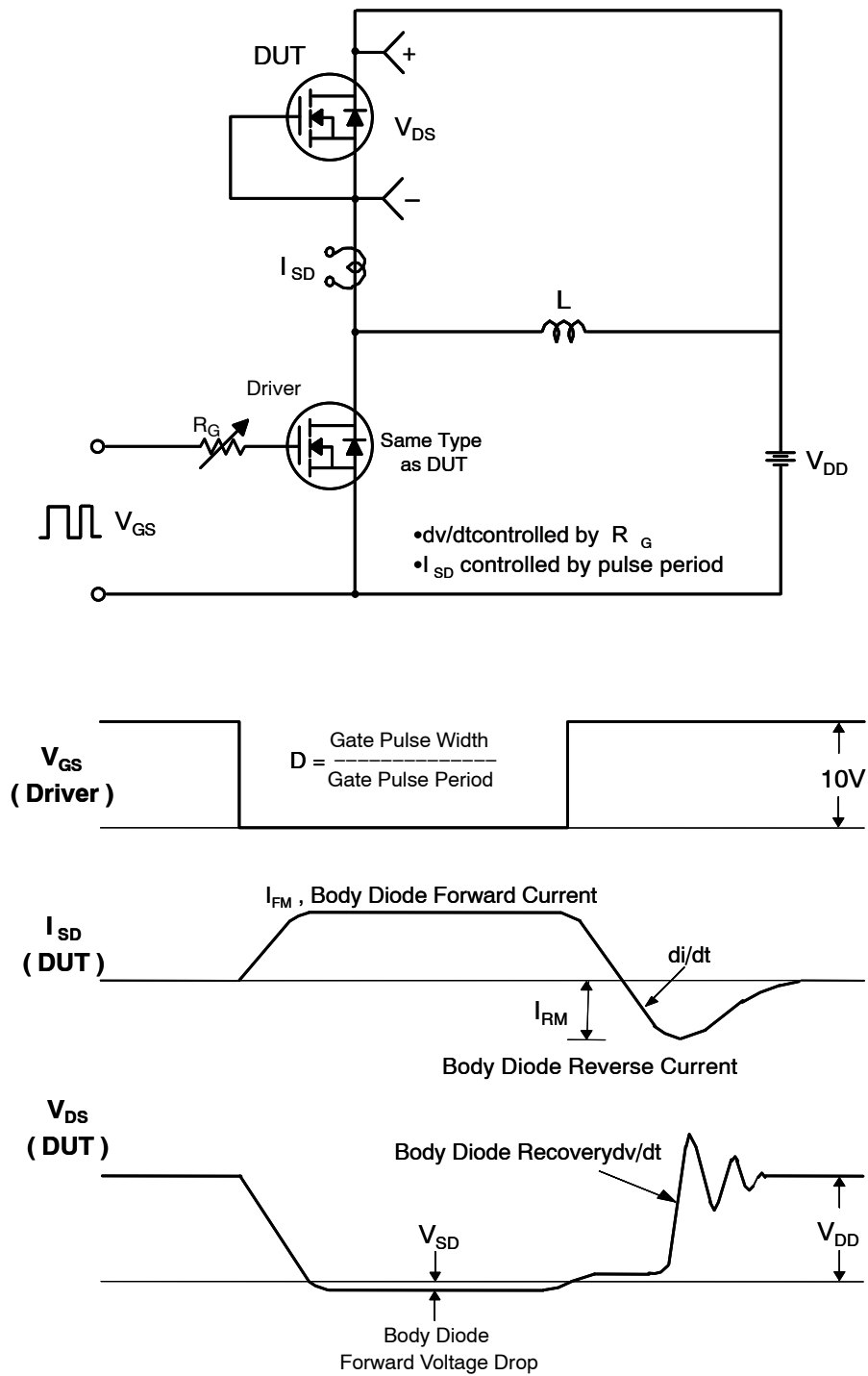


Figure 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms

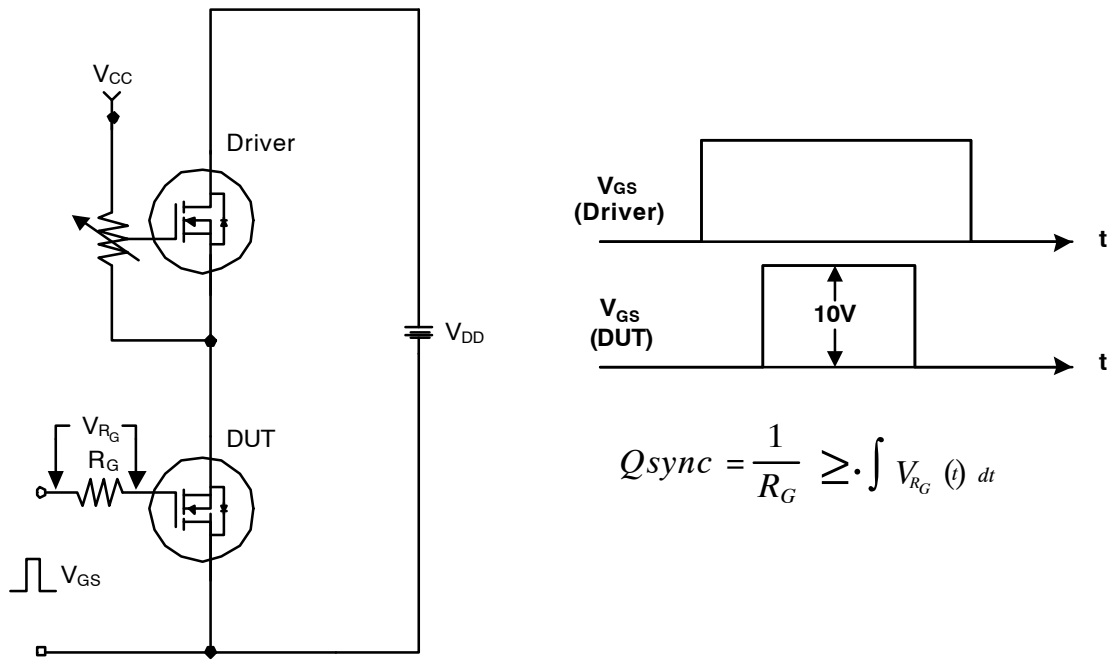
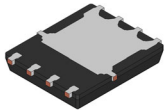


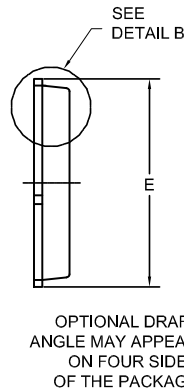
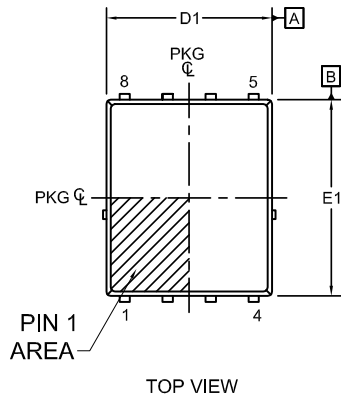
Figure 18. Total Gate Charge Q_{sync} . Test Circuit & Waveforms

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



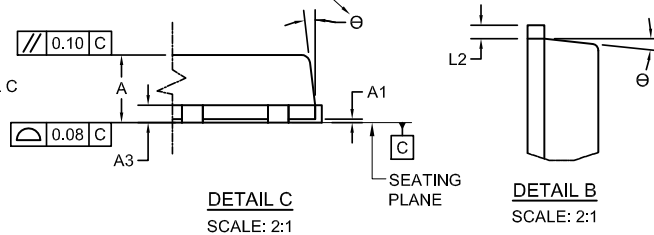
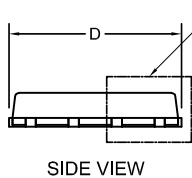
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DATE 21 JAN 2022

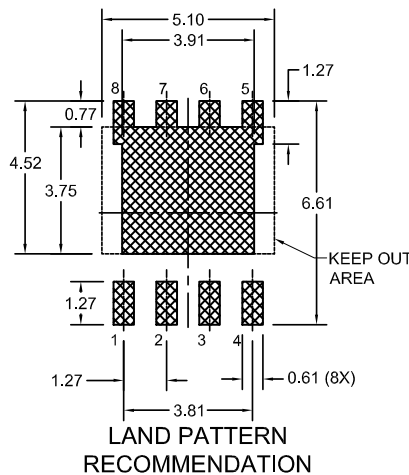
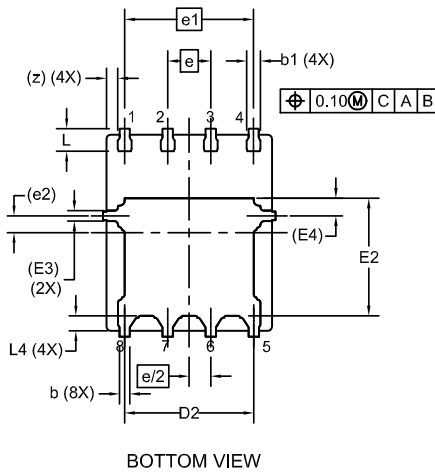


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.
6. IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	-	0.05
b	0.21	0.31	0.41
b1	0.31	0.41	0.51
A3	0.15	0.25	0.35
D	4.90	5.00	5.20
D1	4.80	4.90	5.00
D2	3.61	3.82	3.96
E	5.90	6.15	6.25
E1	5.70	5.80	5.90
E2	3.38	3.48	3.78
E3	0.30 REF		
E4	0.52 REF		
e	1.27 BSC		
e/2	0.635 BSC		
e1	3.81 BSC		
e2	0.50 REF		
L	0.51	0.66	0.76
L2	0.05	0.18	0.30
L4	0.34	0.44	0.54
z	0.34 REF		
θ	0°	-	12°



*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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